

NTD3055-150-1G Information



For Reference Only

Part Number NTD3055-150-1G
Manufacturer ON Semiconductor

Category Discrete Semiconductor Products
Transistors - FETs, MOSFETs - Single

Description MOSFET N-CH 60V 9A IPAK

Package TO-251-3 Short Leads, IPak, TO-251AA

For the pricing/inventory/lead time, please contact

us

Website: https://www.heisener.com E-mail: salesdept@heisener.com



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NTD3055-150-1G Specifications

Manufacturer Part Number NTD3055-150-1G Manufacturer ON Semiconductor Category Discrete Semiconductor Products Transistors - FETs, MOSFETs - Single Package TO-251-3 Short Leads, IPak, TO-251AA Series - FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 60V Current - Continuous Drain (Id) @ 25°C 9A (Ta) Drive Voltage (Max Rds On, Min Rds On) 10V Vgs(th) (Max) @ Id 4V @ 250µA Gate Charge (Qg) (Max) @ Vgs 15nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 280F @ 25V Vgs (Max) ±20V FET Feature - Power Dissipation (Max) 1.5W (Ta), 28.8W (Tj) Rds On (Max) @ Id, Vgs 150 mOhm @ 4.5A, 10V Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Through Hole Supplier Device Package I-Pak Package / Case TO-251-3 Short Leads, IPak, TO-251AA		
Category Discrete Semiconductor Products Transistors - FETs, MOSFETs - Single Package TO-251-3 Short Leads, IPak, TO-251AA Series - FET Type N-Channel Technology MOSFET (Metal Oxide) Forain to Source Voltage (Vdss) Current - Continuous Drain (Id) @ 25°C 9A (Ta) Drive Voltage (Max Rds On, Min Rds On) Vgs(th) (Max) @ Id Gate Charge (Qg) (Max) @ Vgs 15nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 280pF @ 25V Vgs (Max) ### 20V FET Feature - Power Dissipation (Max) 1.5W (Ta), 28.8W (Tj) Rds On (Max) @ Id, Vgs 150 mOhm @ 4.5A, 10V Operating Temperature - Supplier Device Package 1-Pak Package / Case Discrete Semiconductor Products Transistors - Single To-251-A Short Leads, IPak, TO-251AA	Manufacturer Part Number	NTD3055-150-1G
Package TO-251-3 Short Leads, IPak, TO-251AA Series - FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 60V Current - Continuous Drain (Id) @ 25°C 9A (Ta) Drive Voltage (Max Rds On, Min Rds On) 10V Vgs(th) (Max) @ Id 4V @ 250μA Gate Charge (Qg) (Max) @ Vgs 15nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 280pF @ 25V Vgs (Max) ±20V FET Feature - Power Dissipation (Max) 1.5W (Ta), 28.8W (Tj) Rds On (Max) @ Id, Vgs 150 mOhm @ 4.5A, 10V Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Through Hole Supplier Device Package 1-Pak Package / Case TO-251-3 Short Leads, IPak, TO-251AA	Manufacturer	ON Semiconductor
PackageTO-251-3 Short Leads, IPak, TO-251AASeries-FET TypeN-ChannelTechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)60VCurrent - Continuous Drain (Id) @ 25°C9A (Ta)Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id4V @ 250μAGate Charge (Qg) (Max) @ Vgs15nC @ 10VInput Capacitance (Ciss) (Max) @ Vds280pF @ 25VVgs (Max)±20VFET Feature-Power Dissipation (Max)1.5W (Ta), 28.8W (Tj)Rds On (Max) @ Id, Vgs150 mOhm @ 4.5A, 10VOperating Temperature-55°C ~ 175°C (TJ)Mounting TypeThrough HoleSupplier Device PackageI-PakPackage / CaseTO-251-3 Short Leads, IPak, TO-251AA	Category	Discrete Semiconductor Products
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FET TypeN-ChannelTechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)60VCurrent - Continuous Drain (Id) @ 25°C9A (Ta)Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id4V @ 250μAGate Charge (Qg) (Max) @ Vgs15nC @ 10VInput Capacitance (Ciss) (Max) @ Vds280pF @ 25VVgs (Max)±20VFET Feature-Power Dissipation (Max)1.5W (Ta), 28.8W (Tj)Rds On (Max) @ Id, Vgs150 mOhm @ 4.5A, 10VOperating Temperature-55°C ~ 175°C (TJ)Mounting TypeThrough HoleSupplier Device PackageI-PakPackage / CaseTO-251-3 Short Leads, IPak, TO-251AA	Package	TO-251-3 Short Leads, IPak, TO-251AA
TechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)60VCurrent - Continuous Drain (Id) @ 25°C9A (Ta)Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id4V @ 250μAGate Charge (Qg) (Max) @ Vgs15nC @ 10VInput Capacitance (Ciss) (Max) @ Vds280pF @ 25VVgs (Max)±20VFET Feature-Power Dissipation (Max)1.5W (Ta), 28.8W (Tj)Rds On (Max) @ Id, Vgs150 mOhm @ 4.5A, 10VOperating Temperature-55°C ~ 175°C (TJ)Mounting TypeThrough HoleSupplier Device PackageI-PakPackage / CaseTO-251-3 Short Leads, IPak, TO-251AA	Series	-
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Current - Continuous Drain (Id) @ 25°C Prive Voltage (Max Rds On, Min Rds On) Vgs(th) (Max) @ Id Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) FET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs 150 mOhm @ 4.5A, 10V Operating Temperature Supplier Device Package Package / Case Power Dissipation (Pax) Through Hole To-251-3 Short Leads, IPak, TO-251AA	Technology	MOSFET (Metal Oxide)
Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id4V @ 250μAGate Charge (Qg) (Max) @ Vgs15nC @ 10VInput Capacitance (Ciss) (Max) @ Vds280pF @ 25VVgs (Max)±20VFET Feature-Power Dissipation (Max)1.5W (Ta), 28.8W (Tj)Rds On (Max) @ Id, Vgs150 mOhm @ 4.5A, 10VOperating Temperature-55°C ~ 175°C (TJ)Mounting TypeThrough HoleSupplier Device PackageI-PakPackage / CaseTO-251-3 Short Leads, IPak, TO-251AA	Drain to Source Voltage (Vdss)	60V
Vgs(th) (Max) @ Id Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) +20V FET Feature - Power Dissipation (Max) Rds On (Max) @ Id, Vgs Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Through Hole Supplier Device Package Package / Case TO-251-3 Short Leads, IPak, TO-251AA	Current - Continuous Drain (Id) @ 25°C	9A (Ta)
Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds 280pF @ 25V Vgs (Max) ±20V FET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs 150 mOhm @ 4.5A, 10V Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Through Hole Supplier Device Package I-Pak Package / Case TO-251-3 Short Leads, IPak, TO-251AA	Drive Voltage (Max Rds On, Min Rds On)	10V
Input Capacitance (Ciss) (Max) @ Vds 280pF @ 25V Vgs (Max) ±20V FET Feature - Power Dissipation (Max) Rds On (Max) @ Id, Vgs 1.5W (Ta), 28.8W (Tj) Rds On (Max) @ Id, Vgs 150 mOhm @ 4.5A, 10V Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Through Hole Supplier Device Package I-Pak Package / Case TO-251-3 Short Leads, IPak, TO-251AA	Vgs(th) (Max) @ Id	4V @ 250μA
Vgs (Max)±20VFET Feature-Power Dissipation (Max)1.5W (Ta), 28.8W (Tj)Rds On (Max) @ Id, Vgs150 mOhm @ 4.5A, 10VOperating Temperature-55°C ~ 175°C (TJ)Mounting TypeThrough HoleSupplier Device PackageI-PakPackage / CaseTO-251-3 Short Leads, IPak, TO-251AA	Gate Charge (Qg) (Max) @ Vgs	15nC @ 10V
FET Feature - Power Dissipation (Max) 1.5W (Ta), 28.8W (Tj) Rds On (Max) @ Id, Vgs 150 mOhm @ 4.5A, 10V Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Through Hole Supplier Device Package I-Pak Package / Case TO-251-3 Short Leads, IPak, TO-251AA	Input Capacitance (Ciss) (Max) @ Vds	280pF @ 25V
Power Dissipation (Max) Rds On (Max) @ Id, Vgs 150 mOhm @ 4.5A, 10V Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Through Hole Supplier Device Package I-Pak Package / Case TO-251-3 Short Leads, IPak, TO-251AA	Vgs (Max)	±20V
Rds On (Max) @ Id, Vgs 150 mOhm @ 4.5A, 10V Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Through Hole Supplier Device Package I-Pak Package / Case TO-251-3 Short Leads, IPak, TO-251AA	FET Feature	-
Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Through Hole Supplier Device Package I-Pak Package / Case TO-251-3 Short Leads, IPak, TO-251AA	Power Dissipation (Max)	1.5W (Ta), 28.8W (Tj)
Mounting Type Through Hole Supplier Device Package I-Pak Package / Case TO-251-3 Short Leads, IPak, TO-251AA	Rds On (Max) @ Id, Vgs	150 mOhm @ 4.5A, 10V
Supplier Device Package I-Pak Package / Case TO-251-3 Short Leads, IPak, TO-251AA	Operating Temperature	-55°C ~ 175°C (TJ)
Package / Case TO-251-3 Short Leads, IPak, TO-251AA	Mounting Type	Through Hole
	Supplier Device Package	I-Pak
Report errors?	Package / Case	TO-251-3 Short Leads, IPak, TO-251AA
		Report errors?

NTD3055-150-1G Guarantees



Quality Guarantees

We provide 90 days warranty. *

If the items you received were not in perfect quality, we would be responsible for your refund or replacement, but the items must be returned in their original condition.



Service Guarantees

We guarantee 100% customer satisfaction.

Our experienced sales team and tech support team back our services to satisfy all our customers.

NTD3055-150-1G Payment Methods



















NTD3055-150-1G Shipping Methods













If you have any question about NTD3055-150-1G, please do not hesitate to contact us!

Website: https://www.heisener.com E-mail: salesdept@heisener.com